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EXAMINER	
TABONE JR, JOHN J	

ART UNIT	PAPER NUMBER
2133	

DATE MAILED: 06/13/2005

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary	Application No.	Applicant(s)	
	10/024,646	KLEVELAND ET AL.	
	Examiner	Art Unit	
	John J. Tabone, Jr.	2133	

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

1)☒ Responsive to communication(s) filed on *12 May 2005*.

2a)☒ This action is **FINAL**. 2b)☐ This action is non-final.

3)☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

4)☒ Claim(s) *1-47* is/are pending in the application.

4a) Of the above claim(s) _____ is/are withdrawn from consideration.

5)☐ Claim(s) _____ is/are allowed.

6)☒ Claim(s) *1-47* is/are rejected.

7)☐ Claim(s) _____ is/are objected to.

8)☐ Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

9)☐ The specification is objected to by the Examiner.

10)☒ The drawing(s) filed on *21 October 2004* is/are: a)☒ accepted or b)☐ objected to by the Examiner.

Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).

Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).

11)☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

12)☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).

a)☐ All b)☐ Some * c)☐ None of:

1.☐ Certified copies of the priority documents have been received.

2.☐ Certified copies of the priority documents have been received in Application No. _____.

3.☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

* See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

1) ☒ Notice of References Cited (PTO-892)
2) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)
3) ☐ Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date _____.
4) ☐ Interview Summary (PTO-413) Paper No(s)/Mail Date. _____.
5) ☐ Notice of Informal Patent Application (PTO-152)
6) ☐ Other: _____.

FINAL DETAILED ACTION

1. Claims 1-47 have been examined.

Response to Amendment

2. Applicant's request for reconsideration of the finality of the rejection of the last Office action is persuasive and, therefore, the finality of that action is withdrawn.

Response to Arguments

3. Applicant's arguments filed 05/12/05 for independent claims 1 and 44 have been considered but are moot in view of the new ground(s) of rejection.

As per arguments for claims 1 and 44:

The Applicant states "As is clearly shown in Figure 5 and described in Fujisaki, the failure analysis memory 5 is not part of the MUT. Accordingly, the purported flag in Fujisaki is not stored in the same memory array that contains the primary block, as required by Claims 1 and 44". The Examiner would like to point out, according to the Applicant's own disclosure in the specification page 5, lines 8-10, the Applicant admits "instead of being part of the same memory array 50, the primary and redundant memory arrays 52, 54 can be separated into two or more memory arrays". Nevertheless, it would have been obvious to one of ordinary skill in the art at the time the invention was made to combine or make integral Fujisaki's failure analysis memory and MUT, since it has been held that forming in one piece an article which has formerly been formed in two

pieces and put together involves only routine skill in the art. *In re Larson*, 144 USPQ 347 (CCPA 1965).

In response to applicant's argument that the examiner's conclusion of obviousness is based upon improper hindsight reasoning, it must be recognized that any judgment on obviousness is in a sense necessarily a reconstruction based upon hindsight reasoning. But so long as it takes into account only knowledge which was within the level of ordinary skill at the time the claimed invention was made, and does not include knowledge gleaned only from the applicant's disclosure, such a reconstruction is proper. See *In re McLaughlin*, 443 F.2d 1392, 170 USPQ 209 (CCPA 1971). The Applicants are also reminded that although the claims are interpreted in light of the specification, limitations from the specification are not read into the claims. See *In re Van Geuns*, 988 F.2d 1181, 26 USPQ2d 1057 (Fed. Cir. 1993).

It is the Examiner's conclusion that independent claims 1 and 44 are not patentably distinct or non-obvious over the prior art of record namely, Fujisaki (US-5831989). Therefore, the rejection is maintained. Based on their dependency on claims 1 and 44, claims 2-17 and 45-47, respectively, stand rejected.

4. Applicant's arguments filed 05/12/05 for independent claims 18 and 36 have been fully considered but they are not persuasive.

<u>As per arguments for claim 18:</u>

The Applicant states "Independent Claim 18 recites while attempting to write to the primary block, determining that an error occurred in writing to the primary block".

The Applicant also states "The phrase "during a test of a memory under test MUT" does not teach determining that an error occurred in writing to the primary block ***"while attempting to write to the primary block"***, as claimed in Claim 18".

The Examiner has carefully considered the Applicants arguments presented on pages 5 and 6 of the current amendment filed 05/12/05. The Examiner also carefully considered pages 8 and 9 of the specification. However, the Examiner can only come to the same conclusion. For example, in reference to the "sense-while-programming technique" disclosed on page 8, lines 21 and 22, the specification states "the programmed state of the memory cell can be sensed while attempting to program the memory cell". This "sense-while-programming technique" which the Examiner understands to be what the Applicants refer to as the "while-attempting-to-write approach" stated above, is broadly interpreted to mean that the "sensing" is a type of reading of the "value" of the cell which is programmed. In light of this, the Examiner asserts that Fujisaki teaches "while attempting to write to the primary block, determining that an error occurred in writing to the primary block".

It is the Examiner's conclusion that independent claims 18 is not patentably distinct or non-obvious over the prior art of record namely, Fujisaki (US-5831989). Therefore, the rejection is maintained. Based on their dependency on claim 18, claims 19-35 stand rejected.

As per arguments for claim 36:

In the previous office action of record the Examiner the following observations:

The Applicants state "Matsumoto et al. fails to teach a three-dimensional memory array

*of vertically-stacked field-**programmable memory cells**". The Applicants also state, "There is no teaching whatsoever in Matsumoto et al. that the memory cells are arranged in a vertical stack to form a three-dimensional memory array, as recited in independent Claim 36". The Examiner would like to point out that Matsumoto suggests the use of a bipolar PROM (programmable read-only memory) as the memory array (**programmable memory cells**). (Col. 9, lines 4-39).* The claim limitation discloses a "type of" **programmable memory cells**. Matsumoto also discloses a "type of" **programmable memory cells** using the PROM (programmable read-only memory). The Examiner asserts the use of a vertical stack to form a three-dimensional memory array is a design choice and cannot constitute patentably of Fujisaki v. Matsumoto et al. In addition, the Examiner refers the Applicants to the specification which states on page 1, lines 20-21, "By way of introduction, the preferred embodiments described below provide a memory device and method for redundancy/self-repair" and on page 3, lines 3-4, "By way of overview, the preferred embodiments described herein relate to redundancy/self-repair operations for a memory array". The Examiner understands the invention to be a method for redundancy/self-repair of a memory device, not a specific memory device. By the Applicants' own admittance the "three-dimensional memory array of vertically-stacked field-programmable memory cells" is a type of memory used, a design choice per say, but it is not limited to that type of memory.

In response to the Applicants' request for a teaching reference the Examiner would like to point out that the prior art is replete with references disclosing the use of stackable programmable memory cells/devices. Gudesen et al., WO-99/14763, A Read-

Only Memory and Read-Only Memory Devices, September 1, 1997, Assignee: OPTICOM is one example. The Examiner wants to emphasize that the ground of rejection for claim 36 is by no means changed and introduces the Gudesen et al. reference for teaching purposes only. Gudesen discloses one or more read-only memories (ROM) may be provided on a semiconductor substrate (1), which also comprises driver and control circuits (13), to accomplish a read-only memory device. Gudesen further suggests the device may be realized either planar or also volumetrically by stacking several read-only memories (ROM) in horizontal layer (15) and connecting them with the substrate (1) via addressing busses (Matsumoto's programmable memory cells using the PROM). See Abstract

It is the Examiner's conclusion that independent claims 36 is not patentably distinct or non-obvious over the prior arts of record namely, Fujisaki (US-5831989) and Matsumoto et al. (US- 5278839). Therefore, the rejection is maintained. Based on their dependency on claim 36, claims 37-43 stand rejected.

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

> A person shall be entitled to a patent unless –
>
> (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

5. Claims 18-20, 22, 23, 25-29, and 35 are rejected under 35 U.S.C. 102(b) as being anticipated by Fujisaki (US-5831989).

Claim 18:

Fujisaki teaches of a redundancy-structured memory under tested MUT has, in addition to a memory cell array (primary block) MCA, row address relief lines SR and column address relief lines SC formed on the periphery of the memory cell array MCA (redundant block of memory cells). Fujisaki also teaches that during a test of a memory under test MUT, a failure data of, for example, logical "1" indicating failure of a memory cell is written in the same address of the failure analysis memory 5 (storing a flag and writing to the redundant block) as that of the memory cell which failed. (Col. 2, lines 10-23, Fig. 6).

Claim 19:

Fujisaki teaches that during a test of a memory under test MUT, a failure data of, for example, logical "1" indicating failure of a memory cell is written in the same address of the failure analysis memory 5 (storing a flag in response to the error in writing to the primary block) as that of the memory cell which failed. (Col. 2, lines 10, 23).

Claim 20:

Fujisaki teaches a flag memory FLM where a flag is stored to indicate the address of the memory under test MUT where the failure has occurred. (Col. 10, lines 17-21).

Claim 22:

Fujisaki teaches that if a failure occurs during a memory test (reading the primary block), the failure signal (flag) is written in an address of the flag memory corresponding

to the address of the memory under test MUT. Fujisaki further discloses at the time of carrying out the failure relief analysis for a tested memory, it is sufficient to read out only the contents of one or more memory blocks corresponding to one or more flag addresses in which a flag of logical "1" has been stored. (Col. 10, lines 13-15; col. 12, lines 24-39).

Claim 23:

Fujisaki teaches that during a test of a memory under test MUT, a failure data of, for example, logical "1" indicating failure of a memory cell is written in the same address of the failure analysis memory 5 (direct mapping) as that of the memory cell which failed. (Col. 2, lines 10-23, Fig. 6).

Claim 25:

Fujisaki teaches as a result of detecting failed cells in the memory under test MUT the defective cell can be replaced by any one of the cells (full-associative mapping) of the address relief lines SR or SC. (Col. 2, lines 10-23, Fig. 6).

Claim 26:

Fujisaki teaches that the failure analysis memory 5 comprises an address formatter FOM_1 (redundancy address matching circuit) for matching an address of a failure memory cell in a memory under test MUT (primary block) with an address of the failure analysis memory 5. (Col. 3, lines 22-25).

Claim 27:

Fujisaki teaches the failure analysis memory (redundant memory) which has the same storage capacity as the memory under test MUT is subdivided into a plurality of

memory blocks and a flag memory. The failure data is written in an address in the failure analysis memory matching that as the MUT (determining the address is written...). Fujisaki teaches at the time the failure relief analysis for the tested memory is executed the contents of one or more memory blocks corresponding to one or more flag addresses is read out (reading the redundant memory). (Col. 12, lines 24,39).

Claim 28:

Fujisaki teaches that of the memory under test is subdivided in its memory area into a plurality of memory blocks (plurality of smaller blocks). Fujisaki also teaches during a test of a memory under test MUT, a failure data of, for example, logical "1" indicating failure of a memory cell (error in writing at least one bit in the smaller block of the primary block) is written in the same address of the failure analysis memory 5. (Col. 2, lines 19-22; col. 12, lines 28,29).

Claim 29:

Fujisaki teaches that the failure analysis memory 5 is subdivided (smaller blocks) into memory blocks of 2^6 (oct-byte) in the row direction, 2^6 in the column direction, and the total 4096 (2^6 X 2^6) (page) memory blocks.

Claim 35:

Fujisaki teaches a memory testing apparatus for testing a semiconductor integrated circuit memory (semiconductor material). (Col. 1, lines 6-10).

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

> (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

6. Claims 1-4, 10, 12, 15, 16, 44 and 47 are rejected under 35 U.S.C. 102(b) as being anticipated by Fujisaki (US-5831989).

Claim 1:

Fujisaki teaches of a redundancy-structured memory under tested MUT has, in addition to a memory cell array (primary block) MCA, row address relief lines SR and column address relief lines SC formed on the periphery of the memory cell array MCA (redundant block of memory cells). Fujisaki also teaches that during a test of a memory under test MUT, a failure data of, for example, logical "1" indicating failure of a memory cell is written in the same address of the failure analysis memory 5 (storing a flag and writing to the redundant block) as that of the memory cell which failed. (Col. 2, lines 10-23, Fig. 6). Fujisaki does nor explicitly teach "the set of memory cells is in the memory array". However, it would have been obvious to one of ordinary skill in the art at the time the invention was made to combine or make integral Fujisaki's failure analysis memory and MUT. The artisan would have been motivated to do so since it has been held that forming in one piece an article which has formerly been formed in two pieces and put together involves only routine skill in the art. *In re Larson*, 144 USPQ 347 (CCPA 1965).

Claim 44:

Fujisaki teaches of a redundancy-structured memory under tested MUT has, in addition to a memory cell array (primary block) MCA, row address relief lines SR and column address relief lines SC formed on the periphery of the memory cell array MCA (redundant block of memory cells). Fujisaki also teaches that during a test of a memory under test MUT, a failure data of, for example, logical "1" indicating failure of a memory cell is written in the same address of the failure analysis memory 5 (storing a flag) as that of the memory cell which failed. (Col. 2, lines 10, 23, Fig. 6). Fujisaki also teaches that if a failure occurs during a memory test (reading the primary block), the failure signal (flag) is written in an address of the flag memory corresponding to the address of the memory under test MUT. Fujisaki further discloses at the time of carrying out the failure relief analysis for a tested memory, it is sufficient to read out only the contents of one or more memory blocks corresponding to one or more flag addresses in which a flag of logical "1" has been stored. (Col. 10, lines 13-15; col. 12, lines 24-39). Fujisaki does nor explicitly teach "the set of memory cells is in the memory array". However, it would have been obvious to one of ordinary skill in the art at the time the invention was made to combine or make integral Fujisaki's failure analysis memory and MUT. The artisan would have been motivated to do so since it has been held that forming in one piece an article which has formerly been formed in two pieces and put together involves only routine skill in the art. *In re Larson*, 144 USPQ 347 (CCPA 1965).

Claim 2:

Fujisaki teaches that if a failure occurs during a memory test (reading the primary block), the failure signal (flag) is written in an address of the flag memory corresponding to the address of the memory under test MUT. Fujisaki further discloses at the time of carrying out the failure relief analysis for a tested memory, it is sufficient to read out only the contents of one or more memory blocks corresponding to one or more flag addresses in which a flag of logical "1" has been stored. (Col. 10, lines 13-15; col. 12, lines 24-39).

Claims 3:

Fujisaki teaches that of the memory under test is subdivided in its memory area into a plurality of memory blocks (plurality of smaller blocks). Fujisaki also teaches during a test of a memory under test MUT, a failure data of, for example, logical "1" indicating failure of a memory cell (error in writing at least one bit in the smaller block of the primary block) is written in the same address of the failure analysis memory 5. (Col. 2, lines 19-22; col. 12, lines 28,29).

Claims 4:

Fujisaki teaches that the failure analysis memory 5 is subdivided (smaller blocks) into memory blocks of 2^6 (oct-byte) in the row direction, 2^6 in the column direction, and the total 4096 (2^6 X 2^6) (page) memory blocks.

Claims 10:

Fujisaki teaches that during a test of a memory under test MUT, a failure data of, for example, logical "1" indicating failure of a memory cell is written in the same address

of the failure analysis memory 5 (direct mapping) as that of the memory cell which failed. (Col. 2, lines 10-23, Fig. 6).

Claim 12:

Fujisaki teaches as a result of detecting failed cells in the memory under test MUT the defective cell can be replaced by any one of the cells (full-associative mapping) of the address relief lines SR or SC. (Col. 2, lines 10-23, Fig. 6).

Claims 15 and 47:

Fujisaki teaches a memory testing apparatus for testing a semiconductor integrated circuit memory (semiconductor material). (Col. 1, lines 6-10).

Claim 16:

7. Fujisaki teaches a flag memory FLM where a flag is stored to indicate the address of the memory under test MUT where the failure has occurred. (Col. 10, lines 17-21).

8. Claims 5-7, 17, 21 and 30-32 are rejected under 35 U.S.C. 103(a) as being unpatentable over Fujisaki (US-5831989) in view of Creta et al. (US-6216247).

Claims 5 and 30:

Fujisaki does not explicitly teach "the error occurs when there is an error in writing a single bit". However, Fujisaki does teach during a test of a memory under test MUT, a failure data of, for example, logical "1" indicating failure of a memory cell (error in writing at least one bit in the smaller block of the primary block) is written in the same address of the failure analysis memory 5. (Col. 2, lines 19-22). Creta teaches data from

main memory 120 and its corresponding ECC value from the ECC memory is passed to a module/circuitry 112 that calculates a "syndrome" based upon the data and the ECC value. Creta also teaches that the syndrome indicates if there is an error and whether or not it can be corrected. Creta discloses a syndrome value of "0" indicates that there is no error in the data. Creta further discloses a syndrome with an odd number of "1"s indicates that a single bit error has occurred. (Col. 3, lines 40-52). It would have been obvious to one of ordinary skill in the art at the time the invention was made to modify Fujisaki's memory testing apparatus to include Creta's ECC memory 125 and module 112. The artisan would have been motivated to do so because this would enable Fujisaki to calculate ECC syndromes and detect single bit errors.

Claims 6 and 31:

The motivation to combine Fujisaki in view of Creta is per claims 5 and 30 above. Creta teaches if the syndrome contains an even number of zeroes, there is a double bit error. (Col. 3, lines 49-51).

Claims 7 and 32:

The motivation to combine Fujisaki in view of Creta is per claims 5 and 30 above. Creta teaches if the syndrome contains an even number of zeroes, there is a double bit or more error which can be detected but cannot be corrected (uncorrectable error). (Col. 3, lines 49-51).

Claims 17 and 21:

The motivation to combine Fujisaki in view of Creta is per claims 5 and 30 above. Creta teaches the use of sending a flag to the processor (host device) in the enhanced

memory controller 500 when a memory error has occurred. The processor can then take measures to correct the fault with ECC technology.

9. Claims 11 and 24 are rejected under 35 U.S.C. 103(a) as being unpatentable over Fujisaki (US-5831989) in view of Rosen (US-6026476).

Claims 11, 24:

Fujisaki does not explicitly teach set-associative mapping. However, Fujisaki does teach of direct and full-associative mapping per rejection of claims 10 and 23 and 12 and 25, respectively above. Fujisaki teaches that this is accomplished via the failure relief analyzer 6, which includes the failure analysis memory 6. (Col. 3, lines 19-28). Rosen teaches of a translation lookaside buffer TLB 22 which can be mapped in accordance with any one of a number of possible mapping policies such as, direct mapping, set-associative mapping, or full-associative mapping. Rosen teaches the TLB 22 simultaneously compares an input address to the virtual address tags in each and every tag line in tag array 23 for full-associative mapping. For set-associative mapping an input address is compared to a set of virtual address tags. It would have been obvious to one of ordinary skill in the art at the time the invention was made to modify Fujisaki's failure relief analyzer 6 to incorporate Rosen's translation lookaside buffer TLB 22 in the address formatter section. The artisan would have been motivated to do so because this would enable Fujisaki to have more versatility in mapping the addresses which are written to the failure analysis memory 6 (redundant memory) via a predefined set of addresses

10. Claim 8, 9, 13, 14, 33, 34, 36, 37, 38, 39, 40, 41, 42, 43, 45, 46, are rejected under 35 U.S.C. 103(a) as being unpatentable over Fujisaki (US-5831989) in view of Matsumoto et al. (US- 5278839).

Claim 36:

Fujisaki teaches of a redundancy-structured memory under tested MUT has, in addition to a memory cell array (primary block) MCA, row address relief lines SR and column address relief lines SC formed on the periphery of the memory cell array MCA (redundant block of memory cells). Fujisaki also teaches that during a test of a memory under test MUT, a failure data of, for example, logical "1" indicating failure of a memory cell is written in the same address of the failure analysis memory 5 (storing a flag and writing to the redundant block) as that of the memory cell which failed. (Col. 2, lines 10, 23). Fujisaki does not explicitly teach the type of memory. However, Fujisaki does teach a memory testing apparatus for testing a semiconductor integrated circuit memory. (Col. 1, lines 6-10). Matsumoto suggests the use of a bipolar PROM (programmable read-only memory) as the memory array (programmable memory cells). (Col. 9, lines 4-39). It would have been obvious to one of ordinary skill in the art at the time the invention was made to replace Fujisaki's memory array with Matsumoto's PROM. The artisan would have been motivated to do so because a bipolar PROM transistor 40 can reduce the size of layout of the memory array, thus saving cost of manufacture.

Claim 37:

Fujisaki teaches that during a test of a memory under test MUT, a failure data of, for example, logical "1" indicating failure of a memory cell is written in the same address of the failure analysis memory 5 (storing a flag in response to the error in writing to the primary block) as that of the memory cell which failed. (Col. 2, lines 10, 23).

Claim 38:

Fujisaki teaches that if a failure occurs during a memory test (reading the primary block), the failure signal (flag) is written in an address of the flag memory corresponding to the address of the memory under test MUT. Fujisaki further discloses at the time of carrying out the failure relief analysis for a tested memory, it is sufficient to read out only the contents of one or more memory blocks corresponding to one or more flag addresses in which a flag of logical "1" has been stored. (Col. 10, lines 13-15; col. 12, lines 24-39).

Claim 39:

Fujisaki teaches that the failure analysis memory 5 comprises an address formatter FOM_1 (redundancy address matching circuit) for matching an address of a failure memory cell in a memory under test MUT (primary block) with an address of the failure analysis memory 5. (Col. 3, lines 22-25).

Claims 8 and 40:

Fujisaki does not explicitly teach "while attempting to program the memory cell, determining that the memory cell is not programmed". However, Fujisaki does teach that during a test of a memory under test MUT, a failure data of, for example, logical "1"

indicating failure of a memory cell is written in the same address of the failure analysis memory 5 as that of the memory cell which failed. (Col. 2, lines 10, 23). Matsumoto suggests the use of a bipolar PROM (programmable read-only memory) as the memory array (programmable memory cells) which is the junction shorting type. Matsumoto teaches that the non-written state of the transistor 40 corresponds to the fused state of the fuse (not in a programmed state). (Col. 9, lines 4-39). It would have been obvious to one of ordinary skill in the art at the time the invention was made to replace Fujisaki's memory array with Matsumoto's PROM. The artisan would have been motivated to do so because programming the bipolar PROM transistor 40 can control the level of the output signal 49 of the programmable fuse.

Claims 9 and 41:

Fujisaki does not explicitly teach "reading the memory cell after the attempt to program the memory cell; and determining that the memory cell is not programmed. However, Fujisaki does teach that during a test of a memory under test MUT, a failure data of, for example, logical "1" indicating failure of a memory cell is written in the same address of the failure analysis memory 5 as that of the memory cell which failed. (Col. 2, lines 10, 23). Matsumoto suggests the use of a bipolar PROM (programmable read-only memory) as the memory array (programmable memory cells) which is the junction shorting type. Matsumoto teaches that the written state of the transistor 40 corresponds to the non-fused state of the fuse (programmed state). Matsumoto teaches a control signal 48 is set at a low level when the redundancy repair is required (after reading the cell). (Col. 9, lines 4-39). It would have been obvious to one of ordinary skill in the art at

the time the invention was made to replace Fujisaki's memory array with Matsumoto's PROM. The artisan would have been motivated to do so because programming the bipolar PROM transistor 40 can control the level of the output signal 49 of the programmable fuse and the programmed state of the transistor 40 can be determined.

Claim 43:

Fujisaki teaches a memory testing apparatus for testing a semiconductor integrated circuit memory (semiconductor material). (Col. 1, lines 6-10).

Claims 13, 33, 42 and 45:

Fujisaki does not explicitly teach the type of memory. However, Fujisaki does teach a memory testing apparatus for testing a semiconductor integrated circuit memory. (Col. 1, lines 6-10). Matsumoto suggests the use of a bipolar PROM (programmable read-only memory) as the memory array (write-once memory cells). (Col. 9, lines 4-39). It would have been obvious to one of ordinary skill in the art at the time the invention was made to replace Fujisaki's memory array with Matsumoto's PROM. The artisan would have been motivated to do so because a bipolar PROM transistor 40 can reduce the size of layout of the memory array, thus saving cost of manufacture.

Claims 14, 34 and 46:

Fujisaki does not explicitly teach the type of memory. However, Fujisaki does teach a memory testing apparatus for testing a semiconductor integrated circuit memory. (Col. 1, lines 6-10). Matsumoto suggests the use of a bipolar PROM (programmable read-only memory) as the memory array (programmable memory cells).

(Col. 9, lines 4-39). It would have been obvious to one of ordinary skill in the art at the time the invention was made to replace Fujisaki's memory array with Matsumoto's PROM. The artisan would have been motivated to do so because a bipolar PROM transistor 40 can reduce the size of layout of the memory array, thus saving cost of manufacture.

Conclusion

Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to John J. Tabone, Jr. whose telephone number is (571) 272-3827. The examiner can normally be reached on M-F.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Albert DeCady can be reached on (571) 272-3819. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

John J. Tabone, Jr.
Examiner
Art Unit 2133

5/26/05

ALBERT DECADY
SUPERVISORY PATENT EXAMINER
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